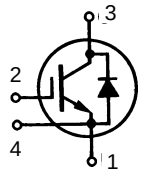
IXYS

High Voltage IGBT with Diode

IXSN 35N120AU1

V_{CES} = 1200 V
I_{C25} = 70 A
$V_{CE(sat)}$ = 4 V

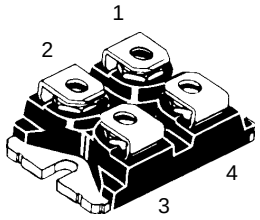


Symbol	Test Conditions		Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C		1200	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ		1200	A
V_{GES}	Continuous		±20	V
V_{GEM}	Transient		±30	V
I_{C25}	T_C = 25°C		70	A
I_{C90}	T_C = 90°C		35	A
I_{CM}	T_C = 25°C, 1 ms		140	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 22 Ω Clamped inductive load, L = 30 µH		I_{CM} = 70 @ 0.8 V_{CES}	A
t_{SC} **(SCSOA)**	V_{GE} = 15 V, V_{CE} = 0.6 • V_{CES}, T_J = 125°C R_G = 22 Ω, non repetitive		10	µs
P_C	T_C = 25°C	IGBT	300	W
P_D		Diode	175	W
V_{ISOL}	50/60 Hz	t = 1 min	2500	V~
	I_{ISOL} ≤ 1 mA	t = 1 s	3000	V~
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
M_d	Mounting torque		1.5/13	Nm/lb.in.
	Terminal connection torque (M4)		1.5/13	Nm/lb.in.
Weight			30	g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 5 mA, V_{GE} = 0 V		1200			V
$V_{GE(th)}$	I_C = 4 mA, V_{CE} = V_{GE}		4		8	V
I_{CES} ①	V_{CE} = 0.8 • V_{CES}	T_J = 25°C			750	µA
	V_{GE} = 0 V	T_J = 125°C			15	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V				4	V

② Device must be heat sunk during high temperature leackage test to avoid thermal runaway.

miniBLOC, SOT-227 B



1 = Emitter ①, 3 = Collector
2 = Gate, 4 = Emitter ①

① Either Emitter terminal can be used as Main or Kelvin Emitter

Features

- International standard package miniBLOC (ISOTOP) compatible
- Aluminium-nitride isolation
  - high power dissipation
- Isolation voltage 3000 V~
- Low $V_{CE(sat)}$
  - for minimum on-state conduction losses
- Fast Recovery Epitaxial Diode
  - short t_{rr} and I_{RM}
- Low collector-to-case capacitance (< 50 pF)
  - reducesd RFI
- Low package inductance (< 10 nH)
  - easy to drive and to protect

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

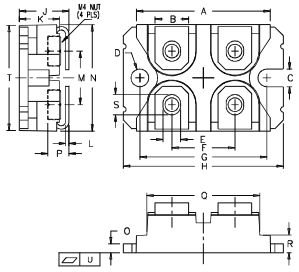
92519E (12/96)

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %	20	26		S
$I_{C(on)}$	V_{CE} = 10 V, V_{GE} = 15 V		170		A
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		3900		pF
C_{oes}			295		pF
C_{res}			60		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		150	190	nC
Q_{ge}			40	60	nC
Q_{gc}			70	100	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		80		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V,		150		ns
$t_{d(off)}$	V_{CE} = 0.8 • V_{CES}, R_G = 2.7 Ω		400	900	ns
t_{fi}	Remarks: Switching times may increase		500	700	ns
E_{off}	for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		10		mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		80		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V,		150		ns
$t_{d(off)}$	V_{CE} = 0.8 • V_{CES}, R_G = 2.7 Ω		400		ns
t_{fi}	Remarks: Switching times may increase		700		ns
E_{on}	for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		6		mJ
E_{off}			15		mJ
R_{thJC}				0.42	K/W
R_{thCK}			0.05		K/W

Reverse Diode (FRED)

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_F	$I_F = I_{C90}$, V_{GE} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			2.35	V
I_{RM}	$I_F = I_{C90}$, V_{GE} = 0 V, -di_F/dt = 480 A/µs		32	35	A
t_{rr}	V_R = 540 V T_J = 100°C		225		ns
	I_F = 1 A; -di/dt = 200 A/µs; V_R = 30 V T_J = 25°C		40	60	ns
R_{thJC}				0.71	K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Fig. 1 Saturation Characteristics

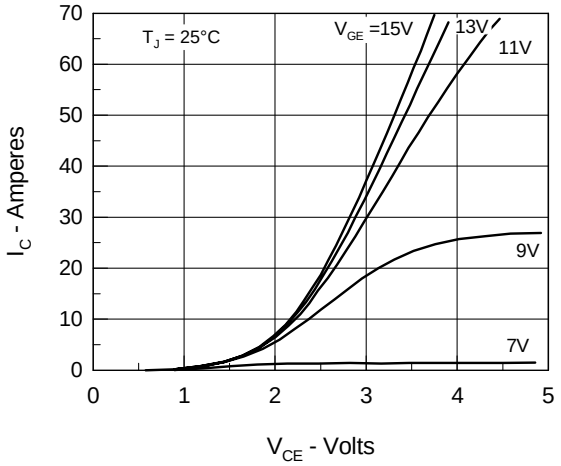


Fig. 2 Output Characterstics

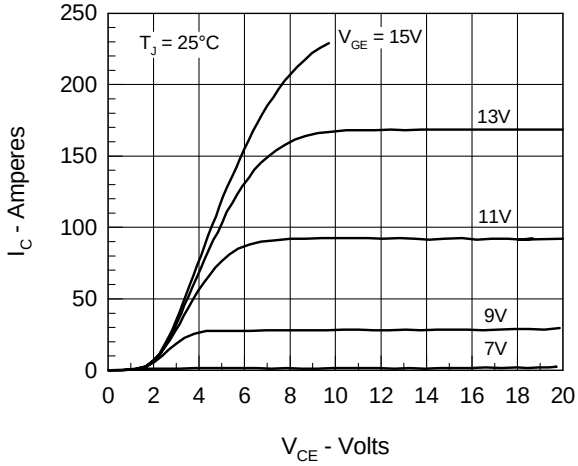


Fig. 3 Collector-Emitter Voltage vs. Gate-Emitter Voltage

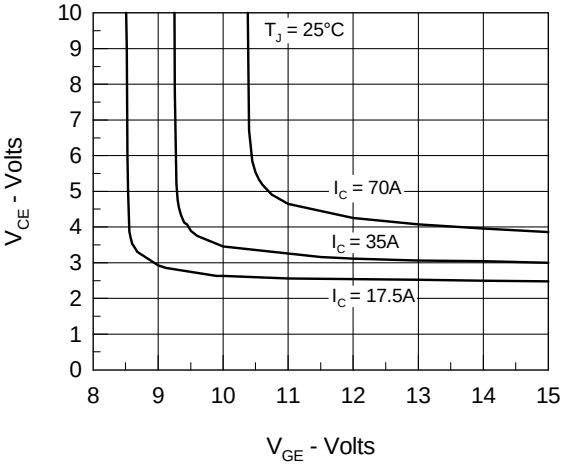


Fig. 4 Temperature Dependence of Output Saturation Voltage

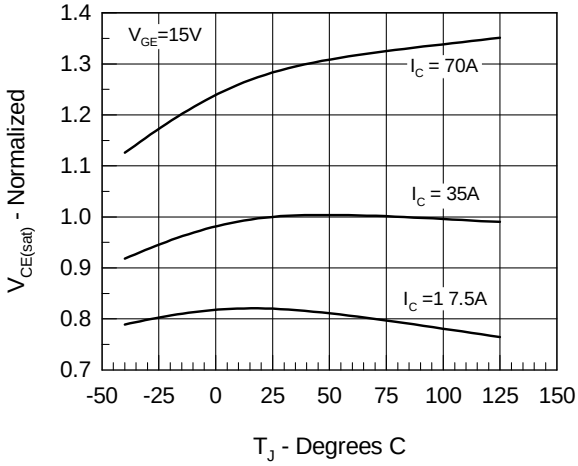


Fig. 5 Input Admittance

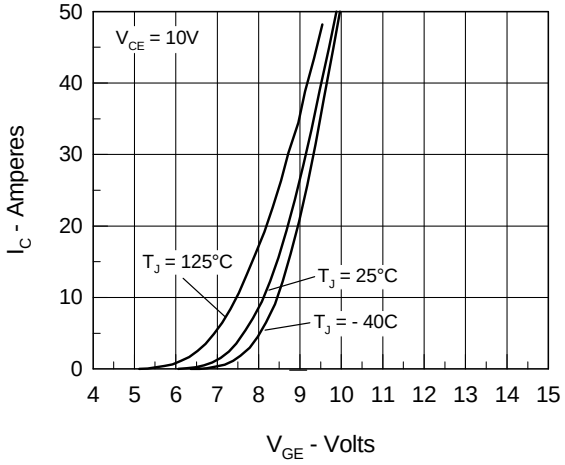


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

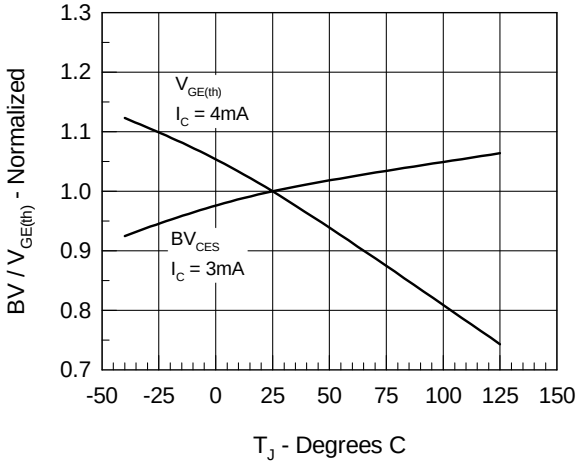


Fig.7 Turn-Off Energy per Pulse and Fall Time on Collector Current

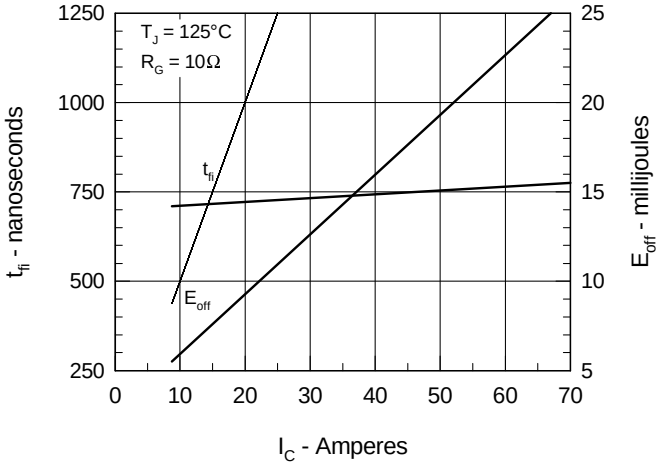


Fig.8 Dependence of Turn-Off Energy Per Pulse and Fall Time on R_G

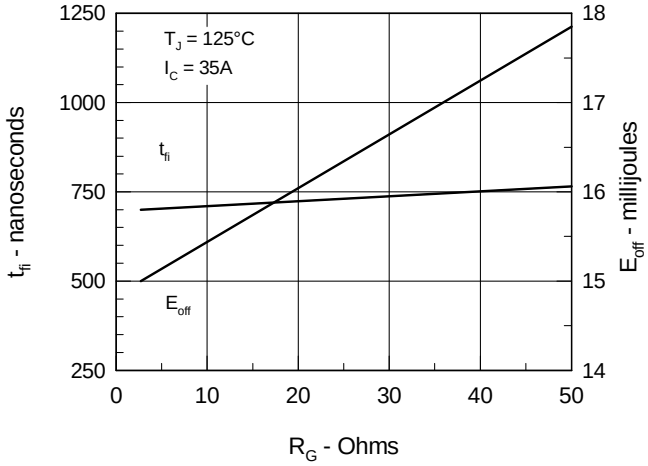


Fig.9 Gate Charge Characteristic Curve

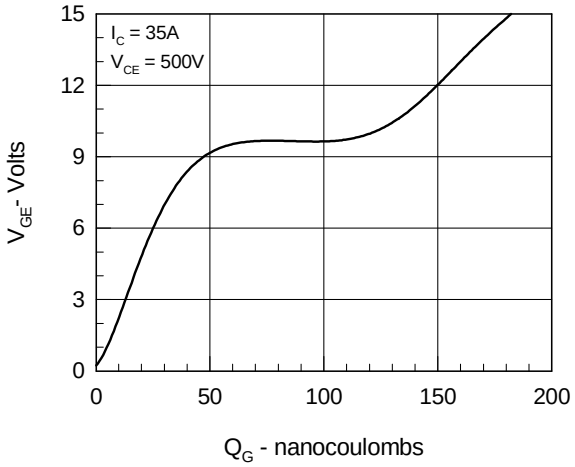


Fig.10 Turn-Off Safe Operating Area

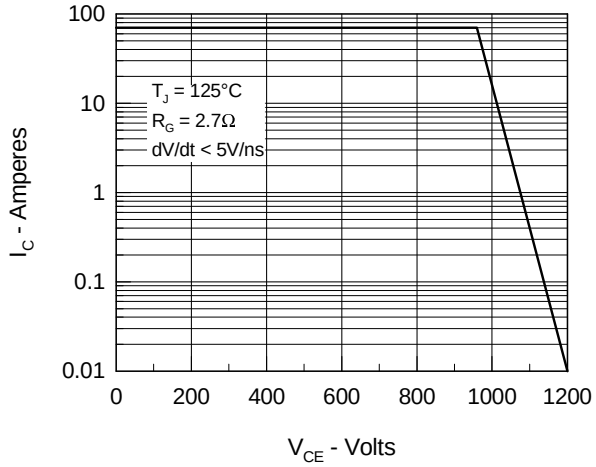


Fig.11 Transient Thermal Impedance